

Course Code	18PYB103J	Course Name	PHYSICS: SEMICONDUCTOR PHYSICS			Course Category	B	Basic Sciences				L	T	P	C										
											3	1	2	5											
Pre-requisite Courses	Nil		Co-requisite Courses	Nil		Progressive Courses	Nil																		
Course Offering Department	Physics and Nanotechnology			Data Book / Codes/Standards		Nil																			
Course Learning Rationale (CLR): The purpose of learning this course is to:																									
CLR-1 :	Introduce band gap and fermi level in semiconductors					Learning			Program Learning Outcomes (PLO)																
CLR-2 :	Explain the concept of carrier transport mechanism in p-n and metal semiconductor junction					1	2	3	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15		
CLR-3 :	Provide an insight on semiconductor optical transitions and photovoltaic effect					Level of Thinking (Bloom)	Expected Proficiency (%)	Expected Attainment (%)	Engineering Knowledge	Problem Analysis	Design & Development	Analysis, Design, Research	Modern Tool Usage	Society & Culture	Environment & Sustainability	Ethics	Individual & Team Work	Communication	Project Mgt & Finance	Life Long Learning	PSO - 1	PSO - 2	PSO - 3		
CLR-4 :	Procure knowledge of electrical and optical measurements in semiconductor								H	H	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
CLR-5 :	Develop necessary skills for low dimensional semiconductor material processing and characterization								H	H	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-
CLR-6 :	Utilize the concepts in physics for the understanding of engineering and technology								H	-	H	-	-	-	-	-	-	-	-	-	-	-	-	-	-
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Course Learning Outcomes (CLO): At the end of this course, learners will be able to:																									
CLO-1 :	Identify the energy band in solids and electron occupation probability					2	85	75																	
CLO-2 :	Analyze the working of optoelectronic devices					2	75	70																	
CLO-3 :	Apply the knowledge to the development of new and novel optoelectronic devices					2	80	75																	
CLO-4 :	Identify the working mechanism of electrical and optical measurements					2	75	70																	
CLO-5 :	Utilize the knowledge of the low dimensional semiconductor material fabrication and characterization.					2	80	70																	
CLO-6 :	Apply the concepts of semiconductor physics in real time applications					2	80	70																	
Duration (hour)	18		18		18		18		18		18		18												
S-1	SLO-1	Classical Free electron theory	Intrinsic semiconductor	Concept of optical transitions in bulk semiconductors	Concept of electrical measurements	Density of states in 2D																			
	SLO-2	Quantum Free electron theory	Fermi level on carrier-concentration and temperature in Intrinsic semiconductor	optical absorption process	Two-point probe technique	Density of states in 1D and 0 D																			
S-2	SLO-1	Density of states	Extrinsic semiconductors	Concept of recombination process	Four-point probe technique-linear method	Introduction to low dimensional systems																			
	SLO-2	Energy band in solids	Fermi level on carrier-concentration and temperature in extrinsic semiconductors	Optical recombination process	Four-point probe technique-Van der Pauw method	Quantum well																			
S-3	SLO-1	Kronig-Penney model	Explanation for carrier generation	Explanation for spontaneous emission	Significance of carrier density	Quantum wire and dots																			
	SLO-2	Kronig-Penney model	Explanation for recombination processes	Explanation for stimulated emission	Significance of resistivity and Hall mobility	Introduction to novel low dimensional systems																			
S-4	SLO-1	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem																			
	SLO-2	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem																			
S-5	SLO-1	Basics of experimentation	Study of I-V characteristics of a light dependent resistor (LDR)	Characterization of pn junction diode (Forward Bias)	Determine Particle Size of Semiconductor Laser	Determine of efficiency of solar cell																			
	SLO-2	Basics of experimentation	Study of I-V characteristics of a light dependent resistor (LDR)	Characterization of pn junction diode (Forward Bias)	Determine Particle Size of Semiconductor Laser	Determine of efficiency of solar cell																			
S-7	SLO-1	E-k diagram	Carrier transport - diffusion and drift current	Joint density of states in semiconductor	Hot-point probe measurement	CNT- properties and synthesis																			
	SLO-2	Direct and Indirect band gap	Continuity equation	Density of states for photons	capacitance-voltage measurements	Applications of CNT																			
S-8	SLO-1	Concept of phonons	p-n junction	Explanation of transition rates	Extraction of parameters in a diode	Fabrication technique-CVD																			
	SLO-2	Concept of Brillouin Zone	Biasing concept in p-n junction	Fermi's golden rule	I-V characteristics of a diode	Fabrication technique-PVD																			

S-9	SLO-1	Energy band structure of semiconductor-Brillouin zone	Metal-semiconductor junction -Ohmic contact	Concept of optical loss	Principle of Deep-level transient spectroscopy (DLTS)	Characterizations techniques for low dimensional systems
	SLO-2	Concept of effective mass	Metal-semiconductor junction - Schottky junction	Concept of optical gain	Instrumentation of DLTS	XRD-Powder method
S-10	SLO-1	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem
	SLO-2	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem
S-11-12	SLO-1	Determine Hall coefficient of Semiconductor material	Determine Band Gap of semiconductor-Four probe method	Repeat/Revision of experiments	Attenuation, propagation characteristic of optical fiber cable using laser source	Determine lattice parameters using powder XRD
	SLO-2	Classification of electronic materials	Semiconductor materials of interest for optoelectronic devices	Basic concepts of Photovoltaics	Significance of band gap in semiconductors	Principle of electron microscopy
S-13	SLO-1	Fermi level	Photocurrent in a P-N junction diode	Photovoltaic effect	Concept of absorption and transmission	Scanning electron microscopy
	SLO-2	Probability of occupation	Light emitting diode	Applications of Photovoltaic effect	Fundamental laws of absorption	Transmission electron microscopy
S-14	SLO-1	Influence of donors in semiconductor	Classification of Light emitting diode	Determination of efficiency of a PV cell	Instrumentation of UV-Vis spectroscopy	Atomic force microscope
	SLO-2	Influence of acceptors in semiconductor	Optoelectronic integrated circuits	Theory of Drude model	Determination of band gap by UV-Vis spectroscopy	Heterojunctions
S-15	SLO-1	Non-equilibrium properties of carriers	Organic light emitting diodes	Determination of conductivity	Concept of Photoluminescence	Band diagrams of heterojunctions
	SLO-2	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem
S-16	SLO-1	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem
	SLO-2	Solving problems	Solving problem	Solving problem	Solving problem	Solving problem
S-17-18	SLO-1	Determine Band Gap of semiconductor-Post Office Box method	Study of V-I and V-R characteristics of a solar cell	To verify Inverse square law of light using a photo cell.	Characteristic of p-n junction diode under reverse bias	Mini Project
	SLO-2					

Learning Resources	1. J. Singh, Semiconductor Optoelectronics: Physics and Technology, McGraw-Hill Inc. 1995.	3. S. M. Sze, Semiconductor Devices: Physics and Technology, Wiley 2008.
	2. B. E. A. Saleh and M. C. Teich, Fundamentals of Photonics, John Wiley & Sons, Inc., 2007.	4. A. Yariv and P. Yeh, Photonics: Optical Electronics in Modern Communications, Oxford University Press, New York 2007.

Learning Assessment											
	Bloom's Level of Thinking	Continuous Learning Assessment (50% weightage)								Final Examination (50% weightage)	
		CLA – 1 (10%)		CLA – 2 (15%)		CLA – 3 (15%)		CLA – 4 (10%)#			
		Theory	Practice	Theory	Practice	Theory	Practice	Theory	Practice	Theory	Practice
Level 1	Remember	20%	20%	15%	15%	15%	15%	15%	15%	15%	15%
	Understand										
Level 2	Apply	20%	20%	20%	20%	20%	20%	20%	20%	20%	20%
	Analyze										
Level 3	Evaluate	10%	10%	15%	15%	15%	15%	15%	15%	15%	15%
	Create										
	Total	100 %		100 %		100 %		100 %		100 %	

CLA – 4 can be from any combination of these: Assignments, Seminars, Tech Talks, Mini-Projects, Case-Studies, Self-Study, MOOCs, Certifications, Conf. Paper etc.,

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
Dr. Vinay Gupta, National Physical Laboratory, guptavinay@nplindia.org	Prof. C. Vijayan, IITM, Chennai, cvijayan@iitm.ac.in	Dr. C. Preferential Kala, SRMIST
	Prof. S. Balakumar, University of Madras, balakumar@unom.ac.in	Dr. M. Krishnamohan, SRMIST